

TRANSISTOR (NPN)

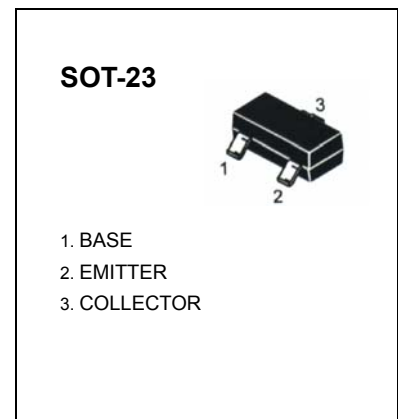
FEATURES

Low equivalent on-resistance

Marking :491

MAXIMUM RATINGS($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1	A
P_C	Collector Power Dissipation	250	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^1$	$I_C=10\text{mA}, I_B=0$	60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=1\text{mA}$	100			
	$h_{FE(2)}^1$	$V_{CE}=5\text{V}, I_C=500\text{mA}$	100		300	
	$h_{FE(3)}^1$	$V_{CE}=5\text{V}, I_C=1\text{A}$	80			
	$h_{FE(4)}^1$	$V_{CE}=5\text{V}, I_C=2\text{A}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)1}^1$	$I_C=500\text{mA}, I_B=50\text{mA}$			0.25	V
	$V_{CE(sat)2}^1$	$I_C=1\text{A}, I_B=100\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}^1$	$I_C=1\text{A}, I_B=100\text{mA}$			1.1	V
Base-emitter voltage	V_{BE}^1	$V_{CE}=5\text{V}, I_C=1\text{A}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{CB}=10\text{V}, f=1\text{MHz}$			10	pF

¹Measured under pulsed conditions, Pulse width=300 μs , Duty cycle $\leq 2\%$.

Typical Characteristics

